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I hereby certify that this correspondence is being deposited via first class mail with the United States Postal Service addressed to : Commissioner of Patents and Trademarks, Alexandria, VA 22313, on March 2005. The applicant and/or attorney requests the date of deposit as the filing date. Depositor: Nitrate Barress Judy Paolillo NICOLE BARRESE

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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In e application of

March 14, 2005

Zhu, et al.

Group Art Unit: 2818

Serial No: 10/708,378

Examiner: Ngo, Ngan V.

Filed: 2/27/04

International Business Machines Corporation

2070 Route 52

Hopewell Junction, NY 12533

TITLE: Hybrid SOI/Bulk Semiconductor Transistors

# **INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the US and non-US patents and publications as listed on Form PTO-1449, attached hereto.

In citing these documents, no representation is made nor intended as to the pertinency or nonpertinency of the art, that better art than that listed is not available, or that other art is not applicable.

No fee is believed to be due for this submission. If any fees are required, however, the Commissioner is hereby authorized to charge such fees to Deposit Account No. 09-0458.

Respectfully submitted,

Zhu, et al.

Joseph P. Abate Registration No. 30,238

Telephone No. 845 894-4633

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		4,665,415	5-12-87	Esaki,	et al.					
		4,853,076	8-1-89	Tsaur,	et al.					
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		JP64-76755	03-1989	Japan						
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		5,134,085	7-28-92	Gilgen	, et al.				
		5,310,446	5-10-94	Konist	ni, et al.				
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		The national Election	Devices Meeting	, 10.7.1, 11.	2000.				
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		International Electron	Devices Meeting,	, IEEE, M	arch 2001.	iique ioi Civio	5-r er formance	Elliancen	en.
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		5,459,346	10-17-95	Asaka	wa, et al.		11.	
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		5,571,741	11-5-96	Leedy			
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		5,683,934	11-4-97	Candela	aria				
		5,840,593	11-24-98	Leedy					
		5,861,651	1-19-99	Brasen,	et al.				
		5,880,040	3-9-99	Sun, et	al.				
		5,940,716	8-17-99	Jin, et a	l				
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	$\Box$	S.R. Sheng, et al., "Deg	gradation and Re	ecovery of Si	Ge HBTs Following Ra	diation and Ho	t-Carrier Stress	ing." Pp.	14-15.
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		5,940,736	8-17-99	Brady, et al.				
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		Devices, vol. 41, no. 4,	April 1994, pp. 5	aded npn-Transistors- Mechanisms 533-38.	allu mayaca	BBB	IVIII	Con C.
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		6,025,280	2-15-00	Brad	y, et al.				Wi King	
		6,046,464	4-4-00	Schetz	tzina					
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		6,090,684	7-18-00	Ishits	suka, et al.					
		6,107,143	8-22-00	Park,	, et al.					
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		6,228,694	5-8-01	Doyle,	et al.				
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		6,265,317	7-24-01	Chiu, e	t al.					
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		6,403,975	6-11-02	Brunne	r, et al.					
		6,406,973	6-18-02	Lee						
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		6,476,462	11-5-02	Shimi	izu, et al.						
		6,483,171	11-19-02	Forbe	es, et al.						
		6,493,497	12-10-02	Ramd	lani, et al.						
		6,498,358	12-24-02	Lach,	et al.						
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		6,501,121	12-31-02	Yu, et	al.					
		6,506,652	1-14-03	Jan, et	al.					
		6,509,618	1-21-03	Jan, et	al.					
		6,521,964	2-18-03	Jan, et	al.					
		6,531,369	3-11-03	Ozkan,	et al.					
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		6,531,740	3-11-03	Bosco, e	t al.			II Area	ROPRIATE	
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